

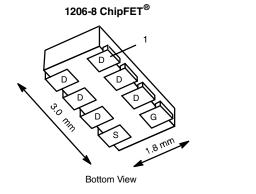
P-Channel 2.5-V (G-S) MOSFET

| PRODUCT SUMMARY | | | | |
|---------------------|------------------------------------|--------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | | |
| - 20 | 0.065 at V _{GS} = - 4.5 V | ± 4.9 | | |
| | 0.074 at V _{GS} = - 3.6 V | ± 4.6 | | |
| | 0.110 at V _{GS} = - 2.5 V | ± 3.8 | | |

FEATURES

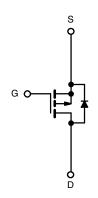
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFETs: 2.5 V Rated





Marking Code

BB XX
Lot Traceability and Date Code
Part # Code



Ordering Information: Si5443DC-T1-E3 (Lead-(Pb)-free)

Si5443DC-T1-GE3 (Lead-(Pb)-free and Halogen-free)

P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS | T _A = 25 °C, unle | ss otherwise n | oted | | | |
|---|------------------------------|-----------------------------------|-------------|--------------|------|--|
| Parameter | | Symbol | 5 s | Steady State | Unit | |
| Drain-Source Voltage | | V _{DS} | - 20 | | V | |
| Gate-Source Voltage | | V _{GS} | ± 12 | | | |
| Continuous Prois Courset /T 150 °C\2 | T _A = 25 °C | I _D | ± 4.9 | ± 3.6 | ^ | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 85 °C | | ± 3.5 | ± 2.6 | | |
| Pulsed Drain Current | | I _{DM} | ± 15 | | Α | |
| Continuous Source Current ^a | | I _{AS} | - 2.1 - 1.1 | | | |
| | T _A = 25 °C | P _D | 2.5 | 1.3 | W | |
| Maximum Power Dissipation ^a | T _A = 85 °C | | 1.3 | 0.7 | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C | |
| Soldering Recommendations (Peak Temperature)b, c | | | 260 | | | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Manimum lumation to Ambient? | t ≤ 5 s | R_{thJA} | 40 | 50 | °C/W |
| Maximum Junction-to-Ambient ^a | Steady State | | 80 | 95 | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 15 | 20 | |

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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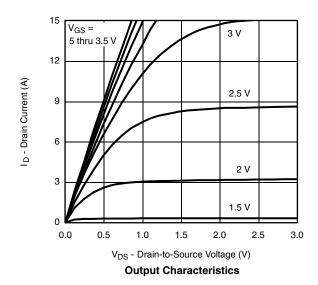
| SPECIFICATIONS $T_J = 25$ °C | C, unless o | otherwise noted | | | | | |
|---|---------------------|--|---|-------|-------|------|--|
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | - 0.6 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$ | V _{DS} = 0 V, V _{GS} = ± 12 V | | ± 100 | nA | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = - 16 V, V _{GS} = 0 V | | - 1 | | | |
| | | V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C | | | - 5 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$ | - 15 | | | Α | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 3.6 A | | 0.056 | 0.065 | Ω | |
| | | V _{GS} = - 3.6 V, I _D = - 3.3 A | | 0.065 | 0.074 | | |
| | | $V_{GS} = -2.5 \text{ V}, I_D = -2.7 \text{ A}$ | | 0.095 | 0.110 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 10 V, I _D = - 3.6 A | | 10 | | S | |
| Diode Forward Voltage ^a | V _{SD} | I _S = - 1.1 A, V _{GS} = 0 V | | - 0.8 | - 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Q_g | | | 9 | 14 | | |
| Gate-Source Charge | Q_{gs} | Q_{gs} $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.6 \text{ A}$ | | 2.2 | | nC | |
| Gate-Drain Charge | Q_{gd} | | | 2.2 | | | |
| Turn-On Delay Time | t _{d(on)} | | | 15 | 25 | | |
| Rise Time | t _r | V_{DD} = - 10 V, R_L = 10 Ω | | 30 | 45 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω | | 50 | 75 | μs | |
| Fall Time | t _f | | | 35 | 50 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = - 1.1 A, dI/dt = 100 A/μs | | 30 | 60 | ns | |

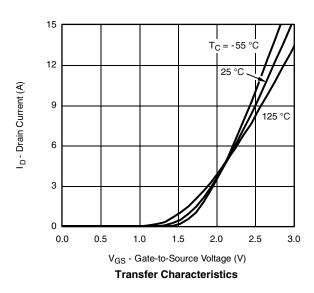
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

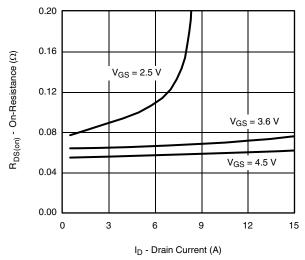
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



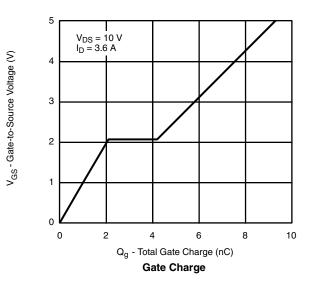




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current

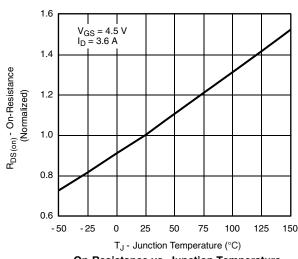


20 T_J = 150 °C 10 T_J = 25 °C 0.2 0.0 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V)

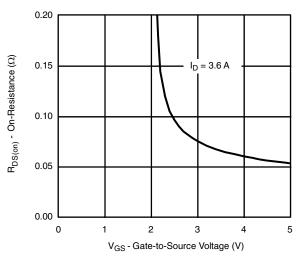
Source-Drain Diode Forward Voltage

1500 1200 Ciss C - Capacitance (pF) 900 600 300 C_{oss} C_{rss} 0 0 8 12 16

V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature



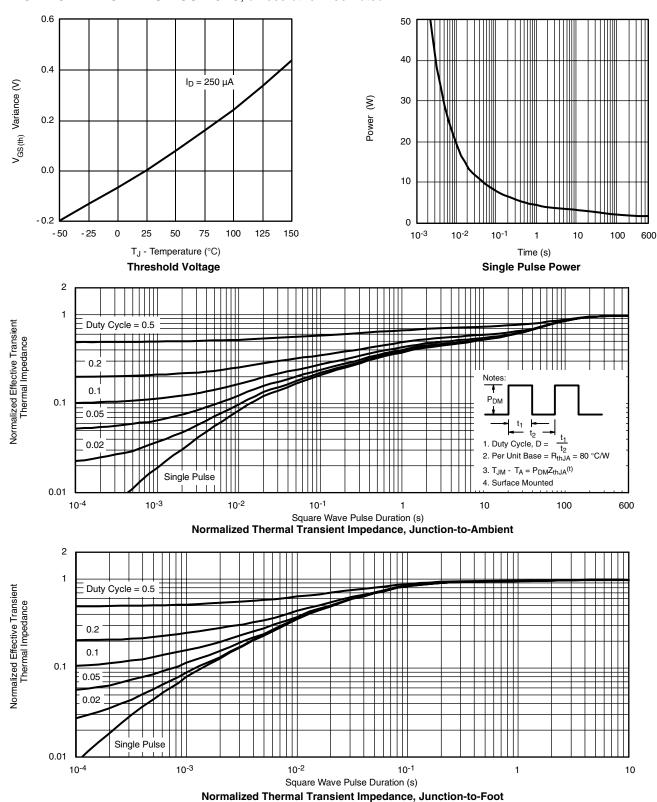
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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